

	Type	L #	Hits	Search Text	DBs	Time Stamp	Corr mm De en ts ni ti on	Er ro rs
1	BRS	L1	862	(MOSFET or IGBT) and (epitax\$5 with diffusion)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 09:13		0
2	BRS	L2	279	(MOSFET or IGBT) and (epitax\$5 with diffusion with implant\$6)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:20		0
3	BRS	L3	544	(MOSFET or IGBT) and (concentration\$1 with profile\$1)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 09:51		0
4	BRS	L4	75	3 and 1	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:14		0
5	BRS	L5	930	(first adj epitax\$6) with (second adj epitax\$6)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:54		0
6	BRS	L6	12	(MOSFET with IGBT) and 5	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:32		0
7	BRS	L7	687	(base with layer with epitax\$6) and (IGBT or MOSFET)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:23		0
8	BRS	L8	208	("base layer" with epitax\$6) and (IGBT or MOSFET)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:24		0
9	BRS	L9	86	(MOSFET or IGBT) and 5	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 10:32		0
10	BRS	L10	249	(second adj epitax\$6) with (high or heavily)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 11:07		0
11	BRS	L14	354	(second adj epitax\$6) with (high\$3 or heavily)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 11:30		0
12	BRS	L17	60	(third adj epitax\$6) with (high\$3 or heavily)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 11:24		0
13	BRS	L18	7637	(second adj layer) with (high\$3 or heavily)	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/06/ 07 11:31		0